



12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN#20260601000.2A

Qualification of MIHO8 as an additional Fab site and DMOS5 METDCU processing for select devices
Change Notification / Sample Request

The rev A is being issued to announce the DMOS5 METDCU processing.

PCN Number:	20260601000.2A		PCN Date:	July 08, 2026																			
Title:	Qualification of MIHO8 as an additional Fab site and DMOS5 METDCU processing for select devices																						
Customer Contact:	Change Management Team		Dept:	Quality Services																			
Proposed 1st Ship Date:	January 04, 2027		Sample requests accepted until:	September 06, 2026*																			
*Sample requests received after September 06, 2026 will not be supported.																							
Change Type:																							
☐	Assembly Site		☐	Design																			
☐	Assembly Process		☐	Data Sheet																			
☐	Assembly Materials		☐	Part number change																			
☐	Mechanical Specification		☐	Test Site																			
☒	Packing/Shipping/Labeling		☐	Test Process																			
☐			☐	Wafer Bump Material																			
☐			☐	Wafer Bump Process																			
☒			☒	Wafer Fab Site																			
☐			☐	Wafer Fab Material																			
☐			☐	Wafer Fab Process																			
PCN Details																							
Description of Change:																							
Texas Instruments is pleased to announce the qualification of MIHO8 as an additional Fab site and DMOS5 for METDCU processing for the devices listed below.																							
<table border="1"><thead><tr><th colspan="3">Current Fab Site</th><th colspan="3">Additional Fab sites</th></tr><tr><th>Current Fab Site</th><th>Process</th><th>Wafer Diameter</th><th>Additional Fab site</th><th>Process</th><th>Wafer Diameter</th></tr></thead><tbody><tr><td>RFAB(Fab) RFAB(METDCU)</td><td>LBC8MVM</td><td>300mm</td><td>MIHO8 (Fab) DM5 (METDCU)</td><td>LBC8MVM</td><td>200mm</td></tr></tbody></table>						Current Fab Site			Additional Fab sites			Current Fab Site	Process	Wafer Diameter	Additional Fab site	Process	Wafer Diameter	RFAB(Fab) RFAB(METDCU)	LBC8MVM	300mm	MIHO8 (Fab) DM5 (METDCU)	LBC8MVM	200mm
Current Fab Site			Additional Fab sites																				
Current Fab Site	Process	Wafer Diameter	Additional Fab site	Process	Wafer Diameter																		
RFAB(Fab) RFAB(METDCU)	LBC8MVM	300mm	MIHO8 (Fab) DM5 (METDCU)	LBC8MVM	200mm																		
**Any PCN sample material received will include all changes announced in the PCN.																							
Qual details are provided in the Qual Data Section.																							
Reason for Change:																							
Supply Continuity																							
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																							
Review the Standard Data Packet for more details on the changes.																							
Impact on Environmental Ratings																							
Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.																							
RoHS		REACH		Green Status																			
☒ No Change		☒ No Change		☒ No Change																			
				IEC 62474																			
				☒ No Change																			

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
RFAB	RFB	USA	Richardson
MIHO8	MH8	JPN	Ibaraki

Sample product shipping label (not actual product label):



Product Affected:

DRV8703QRHBRQ1	DRV3245AQPHPRQ1	DRV3245CQPHPRQ1	DRV3245SQPHPRQ1
TPS7B7702QPWPRQ1			

Product Attributes

Attributes	Qual Device: DRV3245AQPHPRQ1	Qual Device: TPS7B7702QPWPRQ1	Qual Device: DRV8703QRHBRQ1	QBS Process Reference: LM46002AQWPRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Interface	Interface	Power Management
Wafer Fab Supplier	MH8	MH8	MH8	MH8
Assembly Site	TAI	TAI	CDAT	TAI
Package Group	QFP	TSSOP	QFN	TSSOP
Package Designator	PHP	PWP	RHB	PWP
Pin Count	48	16	32	16

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device DRV3245AQPHPRQ1 is qualified at MSL3 260C
- Qual Device TPS7B7702QPWPRQ1 is qualified at MSL3 260C
- Qual Device DRV8703QRHBRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: DRV3245AOPHPRQ1	Qual Device: TPS7B7702QPWPRQ1	Qual Device: DRV8703QRHBRQ1	QBS Process Reference: LM46002AQPWPRQ1
Test Group A - Accelerated Environment Stress Tests											
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	-	-	-	-	3/0/0
HAST	A2	JEDEC JESD22-A110	3	77	Temperature Humidity Bias	85C/85%RH	1000 Hours	-	-	-	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	-	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	-	-	-	1/5/0
PTC	A5	JEDEC JESD22-A105	1	45	PTC	-40/125C	1000 Cycles	-	-	-	1/45/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	3/231/0
Test Group B - Accelerated Lifetime Simulation Tests											
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	1/77/0	-	-	3/231/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	150C	24 Hours	-	-	-	3/2400/0
Test Group C - Package Assembly Integrity Tests											
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	-	3/90/0

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: DRV3245AOPHPRQ1	Qual Device: TPS7B7702QPWPRQ1	Qual Device: DRV8703QRHBRQ1	QBS Process Reference: LM46002AQPWPRQ1
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	-	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	1/15/0
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	-	-	-	3/30/0
Test Group D - Die Fabrication Reliability Tests											
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Tddb	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests											
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	(corner pins only)	750 Volts	1/3/0	1/3/0	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	3	Latch-Up	Per AEC Q100-004	-	1/3/0	1/3/0	1/3/0	1/6/0

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: DRV3245AQPWPRO1	Qual Device: TPS7B7702QPWPRO1	Qual Device: DRV8703QRHBRQ1	QBS Process Reference: LM46002AQPWPRO1
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	3/90/0	3/90/0	3/90/0

Additional Tests

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/HAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2505-068

ZVEI ID: SEM-PW-02, SEM-PW-13, SEM-PS-04

In performing change qualifications, Texas Instruments follows integrated circuit industry standards in performing defect mechanism analysis and failure mechanism-based accelerated environmental testing to ensure wafer fab process, assembly process and product quality and reliability. As encouraged by these standards, TI uses both product-specific and generic (family) data in qualifying its changes. For devices to be categorized as a 'product qualification family' for generic data purposes, they must share similar product, wafer fab process and assembly process elements. The applicability of generic data (also known at TI as Qualification by Similarity (QBS)) is determined by the Reliability Engineering function following these industry standards. Generic data is shown in the qualification report in columns titled "QBS Process" (for wafer fab process), "QBS Package" (for assembly process) and "QBS Product" (for product family).

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.